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(54) **Title:** METHODS OF MICRO-VIA FORMATION FOR ADVANCED PACKAGING

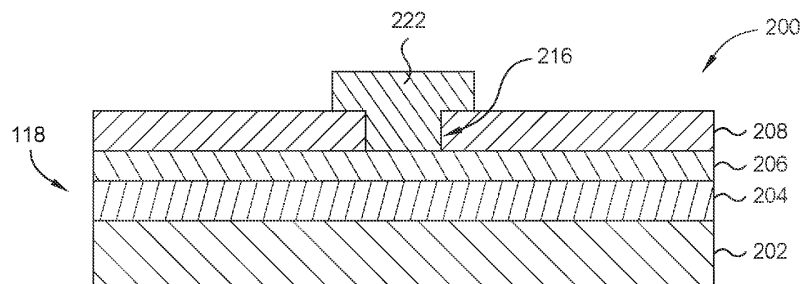


FIG. 2J

(57) **Abstract:** The present disclosure relates to micro-via structures for interconnects in advanced wafer level semiconductor packaging. The methods described herein enable the formation of high-quality, low-aspect-ratio micro-via structures with improved uniformity, thus facilitating thin and small-form-factor semiconductor devices having high I/O density with improved bandwidth and power.

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WO 2022/245512 A1

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